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DUAL 12V PNP LOW SATURATION TRANSISTORS

Features and Benefits

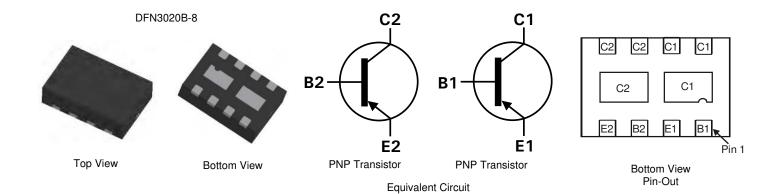
- BV_{CEO} > -12V
- I_C = -4A Continuous Collector Current
- Low Saturation Voltage (-140mV @ -1A)
- R_{SAT} = 60 mΩ for a low equivalent On-Resistance
- h_{FE} specified up to -10A for a high current gain hold up
- Dual NPN saving footprint and component count
- Low profile 0.8mm high package for thin applications
- R_{0.JA} efficient, 40% lower than SOT26
- 6mm² footprint, 50% smaller than TSOP6 and SOT26
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN3020B-8
- Case material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- Nominal package height: 0.8mm
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

Applications

- DC-DC Converters
- Charging circuits
- Power switches
- Motor drive



Ordering Information

I	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXTD717MCTA	D11	7	8	3000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



D11 = Product type marking code Top view, dot denotes pin 1





Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
Collector-Base Voltage		V_{CBO}	-20		
Collector-Emitter Voltage		V_{CEO}	-12	V	
Emitter-Base Voltage		V_{EBO}	-7		
Peak Pulse Current		I _{CM}	-12		
Continuous Collector Current	(Notes 3 & 6)	1-	-4	۸	
Continuous Conector Current	(Notes 4 & 6)	IC	-4.4	^	
Base Current		I_{B}	1		

Thermal Characteristics @ T_A = 25°C unless otherwise specified

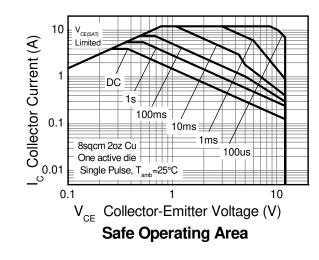
Characteristic	Symbol	Value	Unit	
	(Notes 3 & 6)		1.5 12	
Power Dissipation	(Notes 4 & 6)] _ [2.45 19.6	W
Linear Derating Factor	(Notes 5 & 6)	P _D	1.13 8	mW/°C
	(Notes 5 & 7)	1	1.7 13.6	
	(Notes 3 & 6)		83.3	
Thermal Desistance Investigants Ambient	(Notes 4 & 6)		51.0	
Thermal Resistance, Junction to Ambient	(Notes 5 & 6)	$R_{\theta JA}$	111	°C/W
	(Notes 5 & 7)		73.5	
Thermal Resistance, Junction to Lead (Notes 6 & 8)		$R_{ heta JL}$	17.1	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

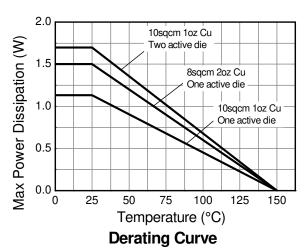
Notes:

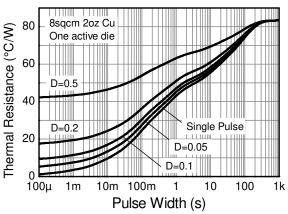
- 3. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.
- 4. Same as note (3), except the device is measured at t <5 sec.
- 5. Same as note (3), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.
- 6. For a dual device with one active die.
- 7. For dual device with 2 active die running at equal power.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

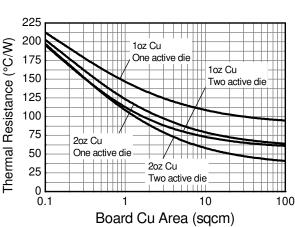


Thermal Characteristics



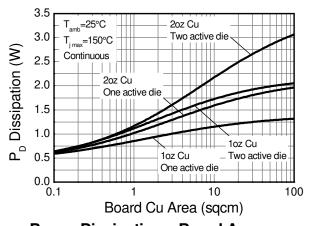






Transient Thermal Impedance

Thermal Resistance v Board Area



Power Dissipation v Board Area





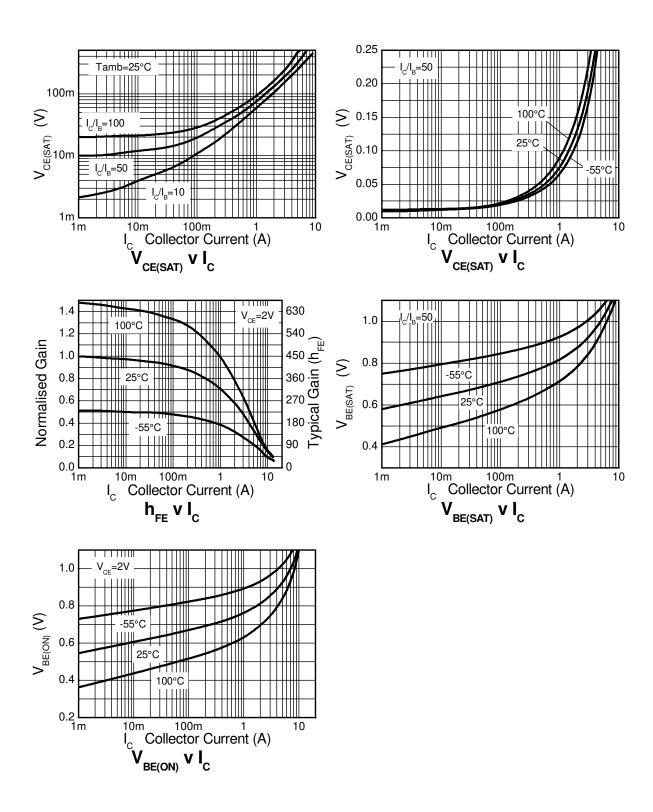
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-20	-35	-	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-12	-25	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.5	-	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	-	-	-100	nA	V _{CB} = -16V
Emitter Cutoff Current	I _{EBO}	-	-	-100	. nA	$V_{EB} = -6V$
Collector Emitter Cutoff Current	I _{CES}	-	-	-100	nA	V _{CES} = -10V
		300	475	-	-	$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
		300	450	-	-	$I_C = -100 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	180	275	-	-	$I_C = -2.5A, V_{CE} = -2V$
		60	100	-	-	$I_{C} = -8A$, $V_{CE} = -2V$
		45	70	-	-	$I_C = -10A$, $V_{CE} = -2V$
		-	-10	-17	mV	$I_C = -0.1A$, $I_B = -10mA$
		-	-100	-140	mV	$I_C = -1A$, $I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	-	-100	-150	mV	$I_C = -1.5A$, $I_B = -50mA$
		-	-195	-300	mV	$I_C = -3A$, $I_B = -50mA$
		-	-240	-310	mV	$I_C = -4A$, $I_{B} = -150mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	-	-0.87	-0.96	V	I _C = -4A, V _{CE} = -2V
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	-	-0.97	-1.07	V	I _C = -4A, I _B = -150mA
Output Capacitance	C _{obo}	-	21	30	pF	V _{CB} = -10V. f = 1MHz
Transition Frequency	f _T	100	110	-	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-on Time	ton	-	70	-	ns	$V_{CC} = -6V, I_{C} = -2A$
Turn-off Time	t _{off}	-	130	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



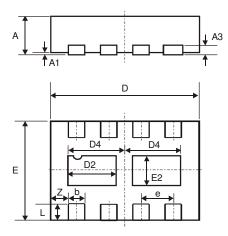
Typical Electrical Characteristics





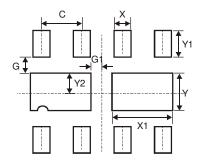


Package Outline Dimensions



DFN3020B-8						
Dim	Min	Max	Тур			
Α	0.77	0.83	0.80			
A1	0	0.05	0.02			
A3	-	1	0.15			
b	0.25	0.35	0.30			
D	2.95	3.075	3.00			
D2	0.82	1.02	0.92			
D4	1.01	1.21	1.11			
е	-	-	0.65			
Е	1.95	2.075	2.00			
E2	0.43	0.63	0.53			
L	0.25	0.35	0.30			
Z	-	-	0.375			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)		
С	0.650		
G	0.285		
G1	0.090		
Х	0.400		
X1	1.120		
Υ	0.730		
Y1	0.500		
Y2	0.365		





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